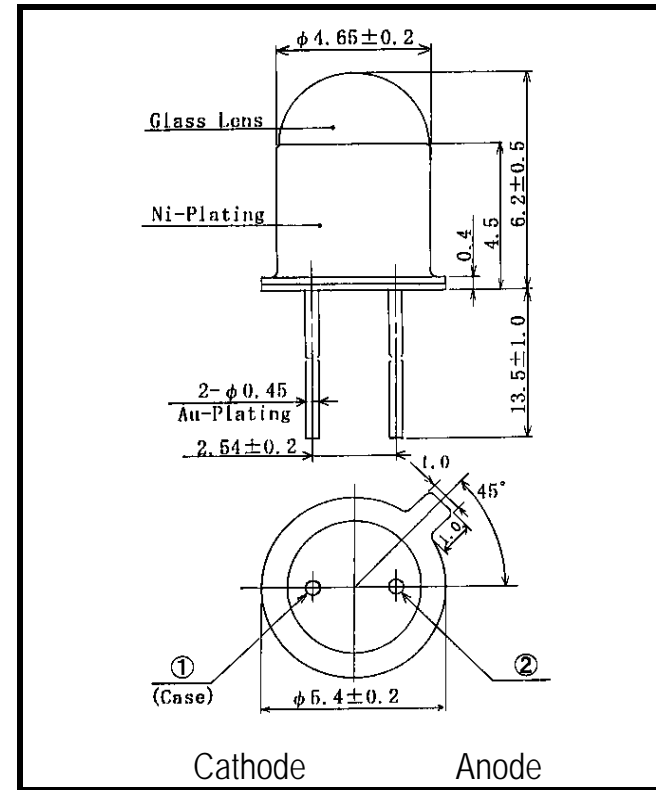


PD150N

Photo Diode



- FEATURES**
- Ultra High Speed
 - Low Dark Current
 - Narrow Angular Response
 - High Reliability in Demanding Environments (Metal Can Package)
- APPLICATIONS**
- Optical Switches
 - Edge Sensing
 - Smoke Detectors

1. ABSOLUTE MAXIMUM RATINGS (Ta=25 °C)

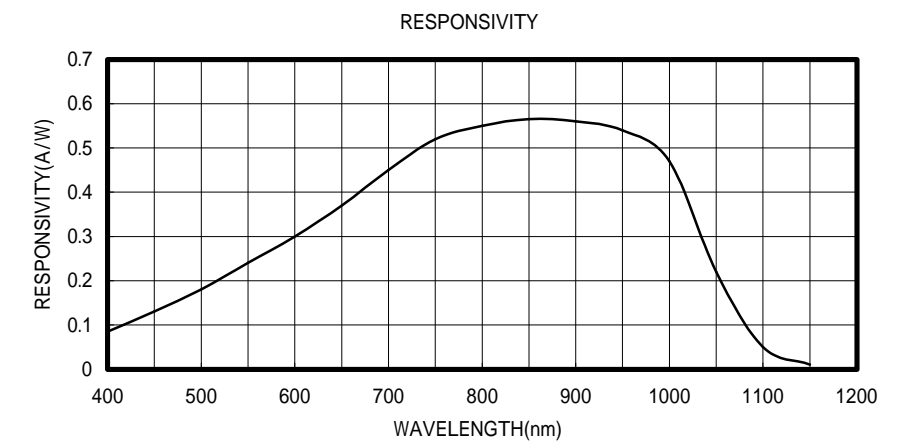
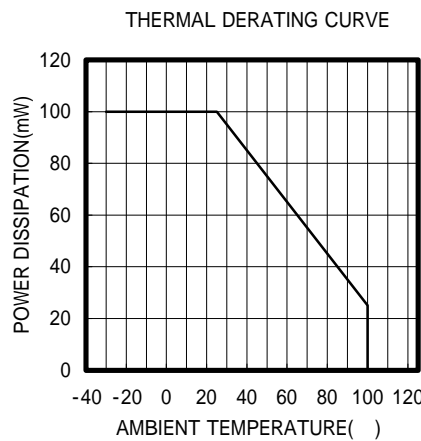
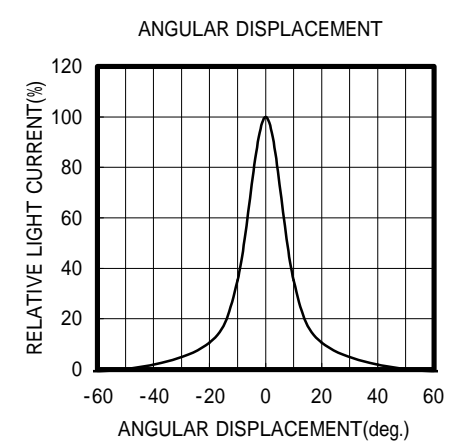
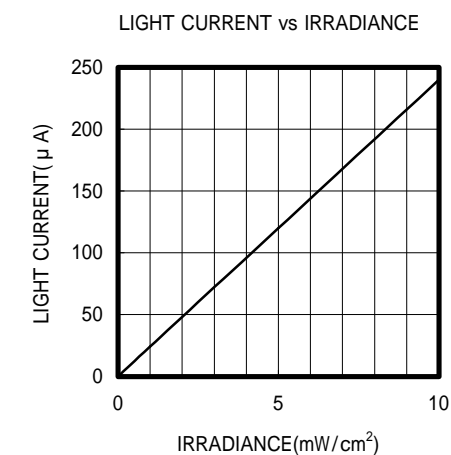
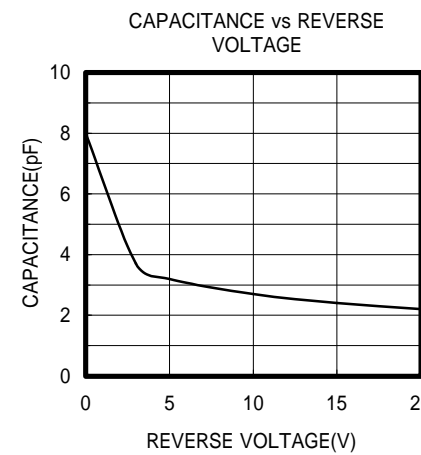
ITEM	SYMBOL	RATINGS	UNIT
Reverse Voltage	VR	30	V
Power Dissipation	PD	100	mW
Operating Temp.	Topr	-30 TO 100	
Storage Temp.	Tstg	-40 TO 125	
Junction Temp.	Tj	100	
Lead Soldering Temp.*1	Tls	260	

*1:Time 5 Sec max,Position:Up to 3mm from the body

2. ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25 °C)

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Light Current	IL	VR=10V, Ee=5mW/cm ²		120		μ A
Dark Current	ID	VR=10V			5	nA
Curve Factor	CF	Ee=5mW/cm ²	0.55			-
Spectral Sensitivity				400 ~ 1100		nm
Peak Sensitivity Wave Length	λ_p			850		nm
Responsivity	Rt	VR=0V, $\lambda=450$ nm		0.20		A/W
Responsivity	Rt	VR=0V, $\lambda=900$ nm		0.55		A/W
Angular Response				± 12		deg
Response Time		RL=50 μ s, Vr=20V		3.5		nS
Junction Capacitance	Cj	at 1MHz, V=0V		8	15	pF

Color Temperature=2870°K Standard Tungsten Lump



OPTRANS

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